AiT Semiconductor Inc.

### DESCRIPTION

The A24C04 provides 4096 bits of Serial Electrically and Programmable Read-Only memory (EEPROM), organized as 512 words of 8 bits each.

The device's cascadable feature allows up to four devices to share a common 2-wire bus. This devise is optimized for use in many industrial and commercial applications where low power and low voltage operation are essential.

The A24C04 is available in SOP8, TSSOP8, DFN8 and TSOT-25 packages operate from 1.7V to 5.5V.

### **ORDERING INFORMATION**

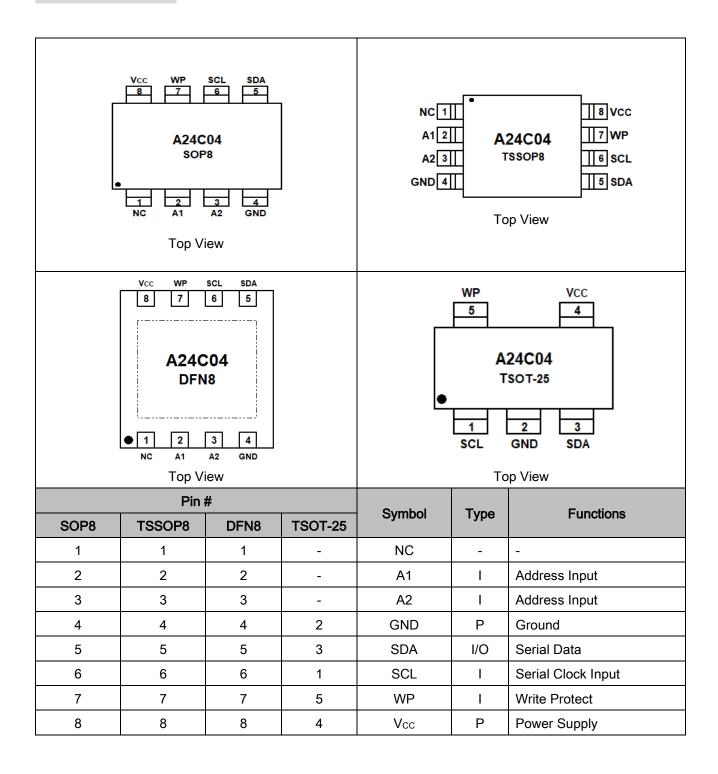
Package Type	Part Number		
SOP8	M8	A24C04M8R	
SPQ: 2,500pcs/Reel	IVIO	A24C04M8VR	
TSSOP8	TMX8	A24C04TMX8R	
SPQ: 3,000pcs/Reel		A24C04TMX8VR	
DFN8	J8	A24C04J8R	
SPQ: 3,000pcs/Reel	J0	A24C04J8VR	
TSOT-25	TE5	A24C04TE5R	
SPQ: 3,000pcs/Reel	A24C04TE5VR		
Note	V: Halogen free Package		
nole	R: Tape & Reel		
AiT provides all R	RoHS products		

### FEATURES

- Wide Range Operation from 1.7V to 5.5C
- Compatible with all I<sup>2</sup>C bidirectional data transfer protocol
- Internally Organized as 512 x 8 (4K)
- Single supply voltage and high speed: 1MHz
- Random and Sequential Read Modes
- 16-byte Page Write Mode:
  Byte Write within 3 ms
  Page Write within 3 ms
  Partial Page Writes Allowed
- Write Protect Pin for Hardware Data Protection
- Schmitt Triggers, Filtered Inputs for Noise Suppression
- High-reliability
  Endurance: 1 Million Write Cycles
  Data Retention: 100 Years
- Enhanced ESD/Latch-up protection HBM KV
- Available in SOP8, TSSOP8, DFN8 and TSOT-25 Packages



## PIN DESCRIPTION





# ABSOLUTE MAXIMUM RATINGS

DC Supply Voltage	-0.3V ~ +6.5V
Input / Output Voltage	GND-0.3V ~ V <sub>CC</sub> +0.3V
Operating Ambient Temperature	-40°C ~ +85°C
Storage Temperature	-65°C ~ +150°C
Electrostatic Pulse (Human Body Model)	6000V

Stress beyond above listed "Absolute Maximum Ratings" may lead permanent damage to the device. These are stress ratings only and operations of the device at these or any other conditions beyond those indicated in the operational sections of the specifications are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### **PIN CAPACITANCE**

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Input / Output Capacitance (SDA)	Cı/o	V <sub>I/O</sub> =0V	-	-	8	pF
Input Capacitance (A1, A2, SCL)	C <sub>IN</sub>	V <sub>IN</sub> =0V	-	-	6	pF

Applicable over recommended operating range from:  $T_A = 25^{\circ}C$ , f = 1.0MHz,  $V_{CC} = +1.7V$ 



## DC ELECTRICAL CHARACTERISTICS

Applicable over recommended operating range from: T <sub>A</sub> = -40°C to +85°C, V <sub>CC</sub> = +1.7V to +5.5V, unless otherwise noted						
Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Supply Voltage	V <sub>CC1</sub>	@400KHz	1.7	-	5.5	V
Supply Voltage	Vcc2	@1MHz	2.5	-	5.5	V
Supply Current $V_{CC}$ = 5.0V	I <sub>CC1</sub>	Read at 400kHz	-	0.14	0.3	mA
Supply Current $V_{CC}$ = 5.0V	Icc2	Write at 400kHz	-	0.28	0.5	mA
Supply Current V <sub>CC</sub> = 5.0V	I <sub>SB1</sub>	$V_{IN} = V_{CC} \text{ or } V_{SS}$	-	0.03	0.5	μA
Input Leakage Current	IL1	$V_{IN} = V_{CC} \text{ or } V_{SS}$	-	0.10	1.0	μA
Output Leakage Current	LO	Vout = Vcc or Vss	-	0.05	1.0	μA
Input Low Level	V <sub>IL1</sub>	$V_{CC}$ = 1.7V to 5.5V	-0.3	-	V <sub>CC</sub> x 0.3	V
Input High Level	VIH1	V <sub>CC</sub> = 1.7V to 5.5V	Vcc x0.7	-	V <sub>CC</sub> + 0.3	V
Output Low Level V <sub>CC</sub> = 1.7V	V <sub>OL1</sub>	I <sub>OL</sub> = 0.15mA	-	-	0.2	V
Output Low Level V <sub>CC</sub> = 3.0V	V <sub>OL2</sub>	I <sub>OL</sub> = 3.0mA	-	-	0.4	V

## AC ELECTRICAL CHARACTERISTICS

Applicable over recommended operating range from:  $T_A = -40^{\circ}C$  to  $+85^{\circ}C$ ,  $V_{CC} = +1.7V$  to +5.5V,  $C_L = 1$  TTL Gate and 100pF, unless otherwise noted

Deremeter	Symbol	1.7V≤V <sub>CC</sub> <2.5V		2.5V≤V <sub>CC</sub> <5.5V			l lait	
Parameter	Symbol	Min.	Тур.	Max.	Min.	Тур.	Max.	Unit
Clock Frequency, SCL	f <sub>SCL</sub>	-	-	400	-	-	1000	kHz
Clock Pulse Width Low	t∟ow	1.3	-	-	0.5	-	-	μs
Clock Pulse Width High	t <sub>HIGH</sub>	0.6	-	-	0.26	-	-	μs
Noise Suppression Time	tı	-	-	50	-	-	50	ns
Clock Low to Data Out Valid	taa	-	-	0.9	-	-	0.45	μs
Time the bus must be free before a new transmission can start	t <sub>BUF</sub>	1.3	-	-	0.5	-	-	μs
Start Hold Time	<b>t</b> hd.sta	0.6	-	-	0.25	-	-	μs
Start Setup Time	<b>t</b> su.sta	0.6	-	-	0.25	-	-	μs
Data In Hold Time	t <sub>HD.DAT</sub>	0	-	-	0	-	-	μs
Data In Setup Time	tsu.dat	100	-	-	100	-	-	ns
Input Rise Time <sup>NOTE1</sup>	t <sub>R</sub>	-	-	0.3	-	-	0.12	μs
Input Fall TimeNOTE1	t⊧	-	-	0.3	-	-	0.12	μs
Stop Setup Time	<b>t</b> su.sто	0.6	-	-	0.25	-	-	μs
Data Out Hold Time	tон	50	-	-	50	-	-	ns
Write Cycle Time	twr	-	1.9	3	-	1.9	3	ms
5.0V, 25°C, Byte Mode <sup>NOTE1</sup>	Endurance	1M	-	-	1M	-	-	Write Cycles

NOTE1: This parameter is characterized and is not 100% tested.

NOTE2: AC measurement conditions:  $R_L$ (connects to V<sub>CC</sub>): 1.3k $\Omega$ 

Input pulse voltages: 0.3  $V_{CC}$  to 0.7  $V_{CC}$ 

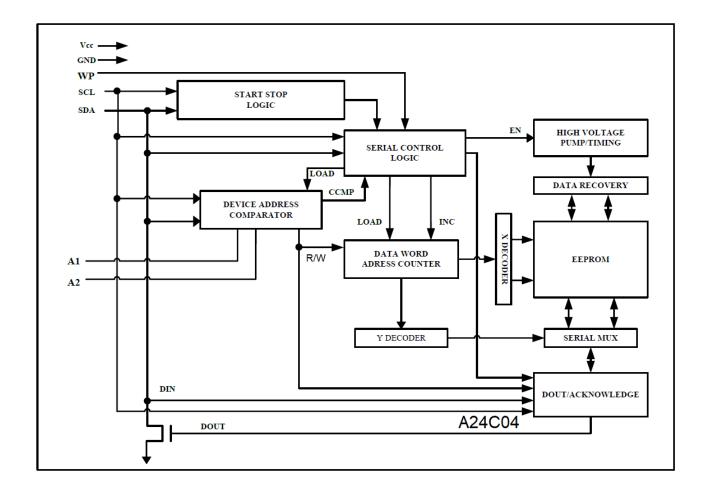
Input rise and fall time: 50ns

Input and output timing reference voltages: 0.5V<sub>CC</sub>

The value of  $R_L$  should be concerned according to the actual loading on the user's system.



# **BLOCK DIAGRAM**





### DETAILED INFORMATION

**DEVICE/PAGE ADDRESSES (A2 and A1):** The A2 and A1 pins are device address inputs that are hard wire for the A24C04. Four 4k devices may be addressed on a single bus system (device addressing is discussed in detail under the Device Addressing section).

**SERIAL DATA (SDA):** The SDA pin is bi-directional for serial data transfer. This pin is open-drain driven and may be wire-ORed with any number of other open-drain or open- collector devices.

**SERIAL CLOCK (SCL):** The SCL input is used to positive edge clock data into each EEPROM device and negative edge clock data out of each device.

**WRITE PROTECT (WP):** The A24C04 has a Write Protect pin that provides hardware data protection. The Write Protect pin allows normal read/write operations when connected to ground (GND). When the Write Protection pin is connected to  $V_{CC}$ , the write protection feature is enabled and operates as shown in the following Table 1.

#### Table1: Write Protect

WP Pin Status	A24C04	
At Vcc	Full Array	
At GND	Normal Read/Write Operations	



### FUNCTIONAL DESCRIPTION

#### 1. Memory Organization

**A24C04, 4k SERIAL EEPROM:** Internally organized with 32 pages of 16 bytes each, the 4K requires a 9- bit data word address for random word addressing.

#### 2. Device Operation

**CLOCK and DATA TRANSITIONS:** The SDA pin is normally pulled high with an external device. Data on the SDA pin may change only during SCL low time periods (see Figure 1 on page 10). Data changes during SCL high periods will indicate a start or stop condition as defined below.

**START CONDITION:** A high-to-low transition of SDA with SCL high is a start condition which must precede any other command (see Figure 2 on page 10).

**STOP CONDITION:** A low-to-high transition of SDA with SCL high is a stop condition. After a read sequence, the stop command will place the EEPROM in a standby power mode (see Figure 2 on page 10).

**ACKNOWLEDGE:** All addresses and data words are serially transmitted to and from the EEPROM in 8-bit words. The EEPROM sends a "0" to acknowledge that it has received each word. This happens during the ninth clock cycle.

**STANDBY MODE:** The A24C04 features a low-power standby mode which is enabled: (a) upon power-up and (b) after the receipt of the STOP bit and the completion of any internal operations.

**MEMORY RESET:** After an interruption in protocol, power loss or system reset, any two-wire part can be reset by following these steps:

- 1. Clock up to 9 cycles.
- 2. Look for SDA high in each cycle while SCL is high.
- 3. Create a start condition.



#### 3. Device Addressing

The 4K EEPROM devices all require an 8-bit device address word following a start condition to enable the chip for a read or write operation (see Figure 4 on page11)

The device address word consists of a mandatory "1", "0" sequence for the first four most significant bits as shown. This is common to all the Serial EEPROM devices.

The 4k EEPROM uses A2 and A1 device address bits to allow as much as for devices on the same bus. These 2 bits must be compared to their corresponding hardwired input pins. The A2 and A1 pins use an internal proprietary circuit that biases them to a logic low condition if the pins are allowed to float.

The eighth bit of the device address is the read/write operation select bit. A read operation is initiated if this bit is high and a write operation is initiated if this bit is low.

Upon a compare of the device address, the EEPROM will output a "0". If a compare is not made, the chip will return to a standby state.

**DATA SECURITY:** The A24C04 has a hardware data protection scheme that allows the user to write protect the entire memory when the WP pin is at  $V_{CC}$ .

#### 4. Write Operations

**BYTE WRITE:** A write operation requires an 8-bit data word address following the device address word and acknowledgment. Upon receipt of this address, the EEPROM will again respond with a "0" and then clock in the first 8-bit data word. Following receipt of the 8-bit data word, the EEPROM will output a "0" and the addressing device, such as a microcontroller, must terminate the write sequence with a stop condition. At this time the EEPROM enters an internally timed write cycle, t<sub>WR</sub>, to the nonvolatile memory. All inputs are disabled during this write cycle and the EEPROM will not respond until the write is complete (see Figure 6 on page11).

**PAGE WRITE:** The 4K EEPROM is capable of a 16-byte page write. A page write is initiated the same as a byte write, but the microcontroller does not send a stop condition after the first data word is clocked in. Instead, after the EEPROM acknowledges receipt of the first data word, the microcontroller can transmit up to seven more data words. The EEPROM will respond with a "0" after each data word received. The microcontroller must terminate the page write sequence with a stop condition (see Figure 7 on page11).

The data word address lower four(4K) bits are internally incremented following the receipt of each data word. The higher data word address bits are not incremented, retaining the memory page row location. When the word address, internally generated, reaches the page boundary, the following byte is placed at the beginning of the same page. If more than sixteen(4K) data words are transmitted to the EEPROM, the data word address will "roll over" and previous data will be overwritten.



**ACKNOWLEDGE POLLING:** Once the internally timed write cycle has started and the EEPROM inputs are disabled, acknowledge polling can be initiated. This involves sending a start condition followed by the device address word. The read/write bit is representative of the operation desired. Only if the internal write cycle has completed will the EEPROM respond with a "0", allowing the read or write sequence to continue.

#### 5. Read Operations

Read operations are initiated the same way as write operations with the exception that the read/write select bit in the device address word is set to "1". There are three read operations: current address read, random address read and sequential read.

**CURRENT ADDRESS READ:** The internal data word address counter maintains the last address accessed during the last read or write operation, incremented by one. This address stays valid between operations as long as the chip power is maintained. The address "roll over" during read is from the last byte of the last memory page to the first byte of the first page. The address "roll over" during write is from the last byte of the current page to the first byte of the same page. Once the device address with the read/write select bit set to "1" is clocked in and acknowledged by the EEPROM, the current address data word is serially clocked out. The microcontroller does not respond with an input "0" but does generate a following stop condition (see Figure 8 on page12).

**RANDOM READ:** A random read requires a "dummy" byte write sequence to load in the data word address. Once the device address word and data word address are clocked in and acknowledged by the EEPROM, the microcontroller must generate another start condition. The microcontroller now initiates a current address read by sending a device address with the read/write select bit high. The EEPROM acknowledges the device address and serially clocks out the data word. The microcontroller does not respond with a "0" but does generate a following stop condition (see Figure 9 on page12)

**SEQUENTIAL READ:** Sequential reads are initiated by either a current address read or a random address read. After the microcontroller receives a data word, it responds with an Acknowledge. As long as the EEPROM receives an Acknowledge, it will continue to increment the data word address and serially clock out sequential data words. When the memory address limit is reached, the data word address will "roll over" and the sequential read will continue. The sequential read operation is terminated when the microcontroller does not respond with a "0" but does generate a following stop condition (see Figure 10 on page12).



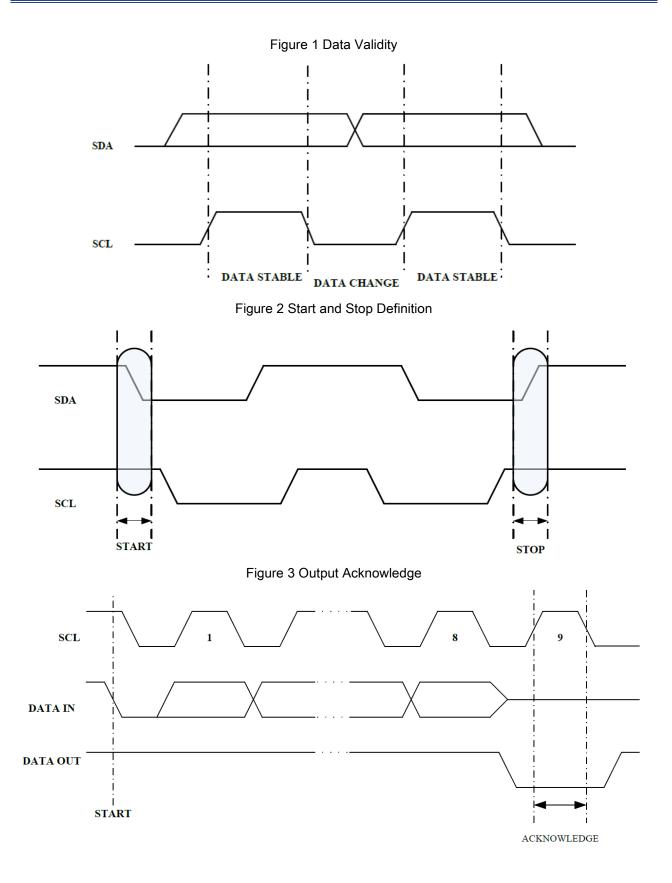
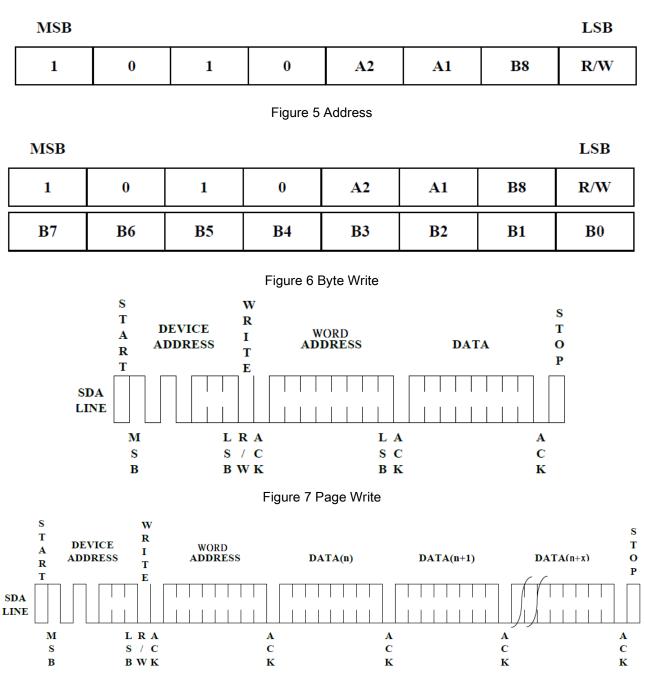
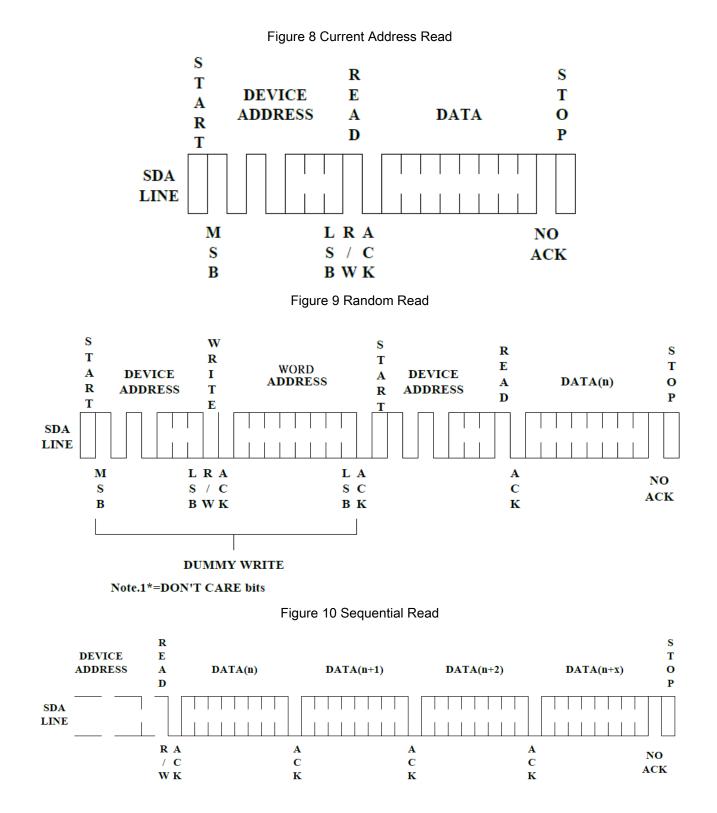




Figure 4 Device Address

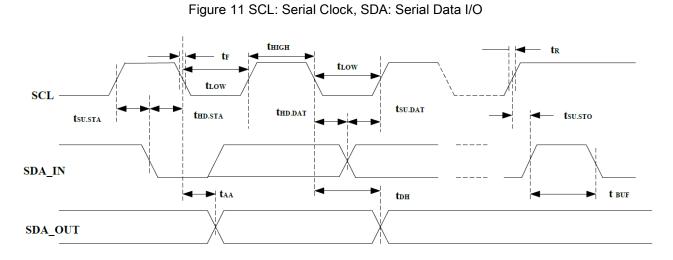




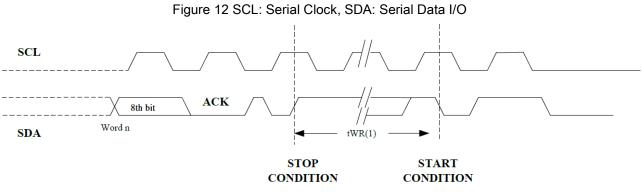




#### **BUS TIMING**



#### WRITE CYCLE TIMING

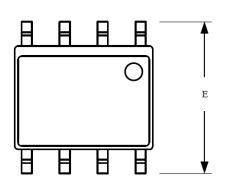


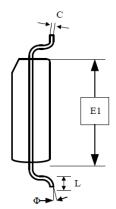
NOTE: The write cycle time t<sub>WR</sub> is the time from a valid stop condition of a write sequence to the end of the internal clear/write cycle.

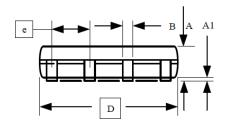


## PACKAGE INFORMATION

Dimension in SOP8 (Unit: mm)



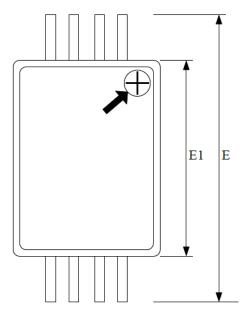


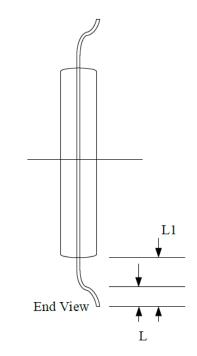


Symbol	Min	Max	
A	1.35	1.75	
A1	0.10	0.23	
В	0.39	0.48	
С	0.21	0.26	
D	4.70	5.10	
E1	3.70	4.10	
E	5.80	6.20	
е	1.27 BSC		
L	0.50	0.80	
θ	0°	8°	

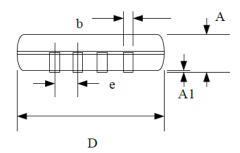


### Dimension in TSSOP8 Package (Unit: mm)





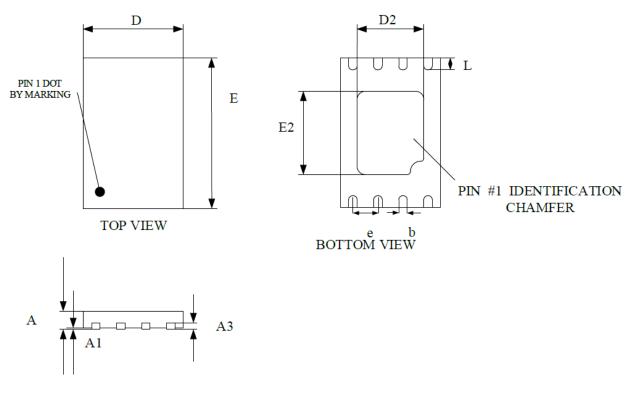




Symbol	Min	Max	
D	2.90	3.10	
E	6.20	6.60	
E1	4.30	4.50	
A	-	1.20	
A1	0.05	0.15	
b	0.21	0.30	
е	0.65 BSC		
L	0.45	0.75	
L1	1.00 REF		



#### Dimension in DFN8 (Unit: mm)

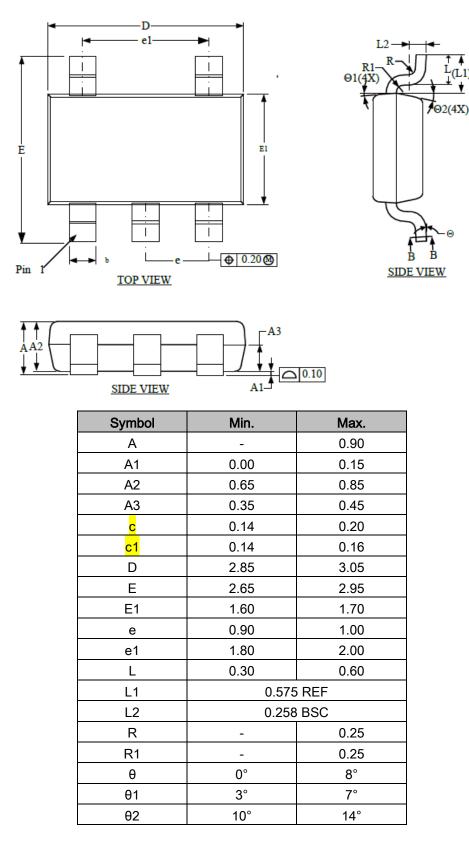


#### SIDE VIEW

Symbol	Min	Max	
А	0.50	0.60	
A1	0.00	0.05	
A3	0.15	REF.	
D	1.95	2.05	
E	2.95	3.05	
b	0.20	0.30	
L	0.20	0.40	
D2	1.25	1.50	
E2	1.15	1.40	
е	0.50 BSC		



#### Dimension in TSOT-25 (Unit: inches)





## IMPORTANT NOTICE

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